## Claims

What is claimed:

1. A semiconductor device, comprising:

a first semiconductor die;

a first conductive layer formed over a first surface of the first semiconductor die; and

a first conductive pillar formed in contact with the first conductive layer, the first conductive pillar including,

a) a body with a first width, and

b) an expanded base with a second width at the first conductive layer greater than the first width,

wherein the expanded base increases in width from the first width to the second width in a linear manner.

2. The semiconductor device of claim 1, further including a conductive via formed in the first semiconductor die.

3. The semiconductor device of claim 2, further including a second conductive layer formed over a second surface of the first semiconductor die opposite the first surface of the first semiconductor die and electrically connected to the conductive via.

4. The semiconductor device of claim 1, further including a second semiconductor die disposed over the first semiconductor die.

5. The semiconductor device of claim 4, further including a second conductive pillar formed over the second

semiconductor die, the second conductive pillar including an expanded base.

6. A semiconductor device, comprising:

a first semiconductor die;

a conductive via extending into the first semiconductor die;

a conductive pillar including a body and an expanded base formed over a first surface of the first semiconductor die and electrically connected to the conductive via, wherein the body has a first width and the expanded base increases in width from the first width to a second width at the first surface of the first semiconductor die; and

a first conductive layer formed over a second surface of the first semiconductor die opposite the first surface of the first semiconductor die and electrically connected to the conductive via.

7. The semiconductor device of claim 6, wherein a width of the expanded base of the conductive pillar is greater than a width of the body of the conductive pillar.

8. The semiconductor device of claim 6, wherein the material of the conductive pillar includes a non-fusible material.

9. The semiconductor device of claim 8, further including a fusible cap formed over the conductive pillar.

10. The semiconductor device of claim 6, further including a second semiconductor die disposed over the first

semiconductor die and electrically connected to the conductive pillar through the conductive via.

11. The semiconductor device of claim 6, further including a second conductive layer formed between the first surface of the first semiconductor die and conductive pillar.

12. A semiconductor device, comprising:

a first semiconductor die;

a conductive via extending into the first semiconductor die; and

a conductive pillar formed over a first surface of the first semiconductor die and electrically connected to the conductive via, wherein the conductive pillar includes a body and an expanded base continuously flared out from a first width of the body to a second width at the first surface of the first semiconductor die.

13. The semiconductor device of claim 12, further including a conductive layer formed over a second surface of the first semiconductor die opposite the first surface of the first semiconductor die and electrically connected to the conductive via.

14. The semiconductor device of claim 12, wherein a width of the expanded base of the conductive pillar is greater than a width of the body of the conductive pillar.

15. The semiconductor device of claim 12, wherein the conductive pillar includes a non-fusible material.

16. The semiconductor device of claim 15, further including a fusible cap formed over the conductive pillar.

17. The semiconductor device of claim 12, further including a second semiconductor die disposed over the first semiconductor die and electrically connected to the conductive pillar through the conductive via.

18. The semiconductor device of claim 12, further including a conductive layer formed between the first surface of the first semiconductor die and conductive pillar.